

Atomic-scale numerical simulation of a nanometer-scale hole etching of SiO₂ with a carbon mask (supplemental document)

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The figures below show the results of the simulation as described in the abstract.

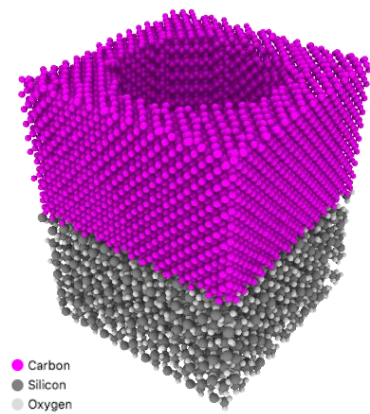


Figure 1. Initial Substrate

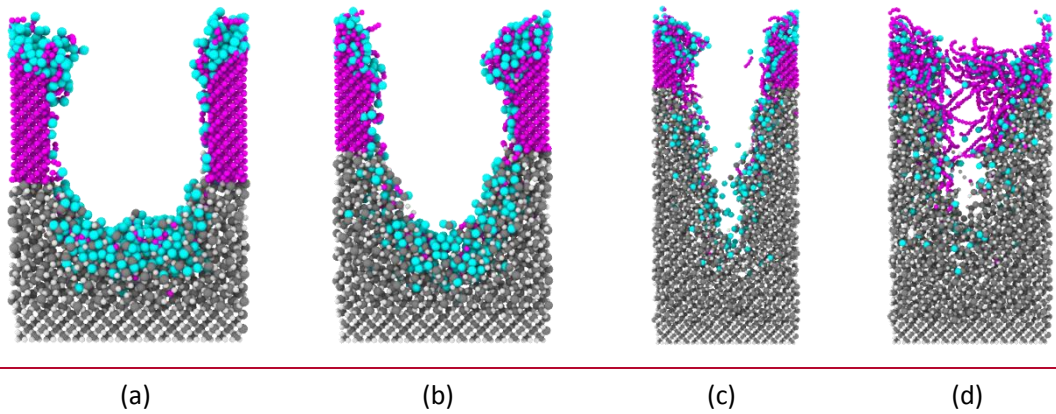


Figure 2. Cross-section images of the substrate after (a) 1163 impacts of 200eV, (b) 1141 impacts of 300eV, (c) 1112 impacts of 500eV, and (d) 845 impacts of 1000eV CF₃⁺ ions